

L Number	Hits	Search Text	DB	Time stamp
1	75475	(laser same (power or energy))	USPAT	2004/02/26 08:32
2	670	((laser same (power or energy))) and (scribe or sribing)	USPAT	2004/02/26 08:33
3	292	((laser same (power or energy))) and (scribe or sribing)) and (pulse or pulsing)	USPAT	2004/02/26 08:33
4	236	((laser same (power or energy))) and (scribe or sribing)) and ((pulse or pulsing) same laser)	USPAT	2004/02/26 08:33
5	213	((laser same (power or energy))) and (scribe or sribing)) and ((pulse or pulsing) with laser)	USPAT	2004/02/26 11:52
6	1	5168454.pn.	USPAT	2004/02/26 09:52
7	1	6281362.pn.	USPAT	2004/02/26 11:53
-	2606	(scribe or scribing or in\$1scrib\$3) and laser and semiconductor	USPAT	2004/02/25 10:39
-	1149	((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)	USPAT	2004/02/23 12:26
-	543	((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)	USPAT	2004/02/23 12:28
-	284	((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma	USPAT	2004/02/23 12:28
-	278	(((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001	USPAT	2004/02/23 12:29
-	263	(((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)	USPAT	2004/02/23 12:31
-	129	((((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing)	USPAT	2004/02/23 13:41
-	7	5149404.URPN.	USPAT	2004/02/23 13:35
-	2	5397420.URPN.	USPAT	2004/02/23 13:39
-	7	("4550257"   "4564736"   "4866238"   "4960495"   "5047649"   "5062364"   "5149404").PN.	USPAT	2004/02/23 13:39
-	9569	(mark or marking) with (substrate or wafer)	USPAT	2004/02/23 13:42
-	612	((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma	USPAT	2004/02/23 13:42
-	405	((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)	USPAT	2004/02/23 13:43

	370	((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)	USPAT	2004/02/23 13:43
	285	((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)	USPAT	2004/02/23 13:44
	276	(((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001	USPAT	2004/02/23 13:44
	261	((((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001) not ((((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing))	USPAT	2004/02/23 13:49
	206	((((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001) not ((((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing)) and (depth or deep)	USPAT	2004/02/23 14:49
	6	("4096619"   "5023188"   "5614445"   "5691248"   "5693181"   "6075280").PN.	USPAT	2004/02/23 14:24
	2078	(scribe or sribing) with (substrate or wafer)	USPAT	2004/02/23 14:49
	245	((scribe or sribing) with (substrate or wafer)) and plasma and semiconductor and laser	USPAT	2004/02/23 14:50
	210	((scribe or sribing) with (substrate or wafer)) and plasma and semiconductor and laser) not ((((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001) not ((((((scribe or sribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing)) and (depth or deep))	USPAT	2004/02/23 14:50

	97	((((scribe or scribing) with (substrate or wafer)) and plasma and semiconductor and laser) not ((((((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001) not (((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing)) and (depth or deep)) and (inert or helium or argon or Ar! or nitrogen or N?sub.2)) and (pit or hole or via or trench or opening))	USPAT	2004/02/23 14:50
	90	((((scribe or scribing) with (substrate or wafer)) and plasma and semiconductor and laser) not ((((((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001) not (((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing)) and (depth or deep)) and (inert or helium or argon or Ar! or nitrogen or N?sub.2)) and (pit or hole or via or trench or opening))	USPAT	2004/02/23 14:51
	85	(((((((scribe or scribing) with (substrate or wafer)) and plasma and semiconductor and laser) not ((((((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001) not ((((((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing)) and (depth or deep)) and (inert or helium or argon or Ar! or nitrogen or N?sub.2)) and (pit or hole or via or trench or opening)) and @ay<=2001)	USPAT	2004/02/23 15:28
	1	6214703.pn.	USPAT	2004/02/23 15:29
	660	laser and (scribe or scribing) and semiconductor and plasma	USPAT	2004/02/23 15:30

	570	(laser and (scribe or scribing) and semiconductor and plasma) not (((((scribe or scribing) with (substrate or wafer)) and plasma and semiconductor and laser) not (((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001) not (((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing)) and (depth or deep)) and (inert or helium or argon or Ar! or nitrogen or N?sub.2)) and (pit or hole or via or trench or opening))	USPAT	2004/02/23 15:30
	462	((laser and (scribe or scribing) and semiconductor and plasma) not (((((scribe or scribing) with (substrate or wafer)) and plasma and semiconductor and laser) not (((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001) not (((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing)) and (depth or deep)) and (inert or helium or argon or Ar! or nitrogen or N?sub.2)) and (pit or hole or via or trench or opening))) and @ay<=2001 and (hole or pit or via or trench or opening))	USPAT	2004/02/23 15:31
	249	((laser and (scribe or scribing) and semiconductor and plasma) not (((((scribe or scribing) with (substrate or wafer)) and plasma and semiconductor and laser) not (((((mark or marking) with (substrate or wafer)) and laser and semiconductor and plasma) and (inert or nitrogen or helium or he or argon or Ar or N?sub.2)) and (pit or via or hole or opening)) and (sacrificial or photo\$1resist or resist)) and @ay<=2001) not (((((scribe or scribing or in\$1scrib\$3) and laser and semiconductor) and (pit or hole)) and (inert or argon or Ar or helium or nitrogen or He or N?sub.2)) and plasma) and @ay<=2001) and (etch or etching or remove or removing)) and (pulse or pulsing)) and (depth or deep)) and (inert or helium or argon or Ar! or nitrogen or N?sub.2)) and (pit or hole or via or trench or opening))) and @ay<=2001 and (hole or pit or via or trench or opening)) and (inert or helium or argon or Ar! or nitrogen or N?sub.2))	USPAT	2004/02/23 15:32

	8	Peiter-Martin.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 17:36
	15	Marx-Eckhard.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 17:36
	15	Mautz-Karl-E.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 17:36
	33	Peiter-Martin.in. or Marx-Eckhard.in. or Mautz-Karl-E.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 17:36